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cancel and
a protrusion formed by a portion not removed of said insulating film in said pad trench to decrease a substantial opening area of said pad trench;

a conductive film buried in said interconnection trench and said pad trench;

a contact hole formed within said pad trench at a position near said protrusion to electrically connect said conductive film to a further conductive film formed below said insulating film, wherein said contact hole and said further conductive film substantially suppress an increase in electrical resistance in said pad trench due to formation of said protrusion.

Subp. 7
8. (Three Times Amended) A semiconductor device, comprising:
a semiconductor substrate;
an insulating film formed on said semiconductor substrate;
an interconnection trench formed on said insulating film and communicating with a semiconductor element;

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a pad trench formed on said insulating film and communicating with said interconnection trench;

a protrusion formed by a portion not removed of said insulating film in said pad trench and reducing a substantial opening area of said pad trench;

a conductive film buried in said interconnection trench and said pad trench;

a further conductive film formed below said insulating film; and

a contact hole formed within said pad trench at least at a position near said protrusion to electrically connect said conductive film to said further conductive film, wherein said contact hole and said further conductive film substantially suppress an increase in electrical resistance in said pad trench due to formation of said protrusion.

Please add new Claims 15 and 16.

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--15. (New Claim) A damascene interconnection according to claim 1, wherein said hole is located to surround said protrusion.